

High Reliability 2.0-inch Dual-Color 5mm 5x7 Dot Matrix LED Displays

SDM-5572 SDM-5579

GENERAL DESCRIPTION

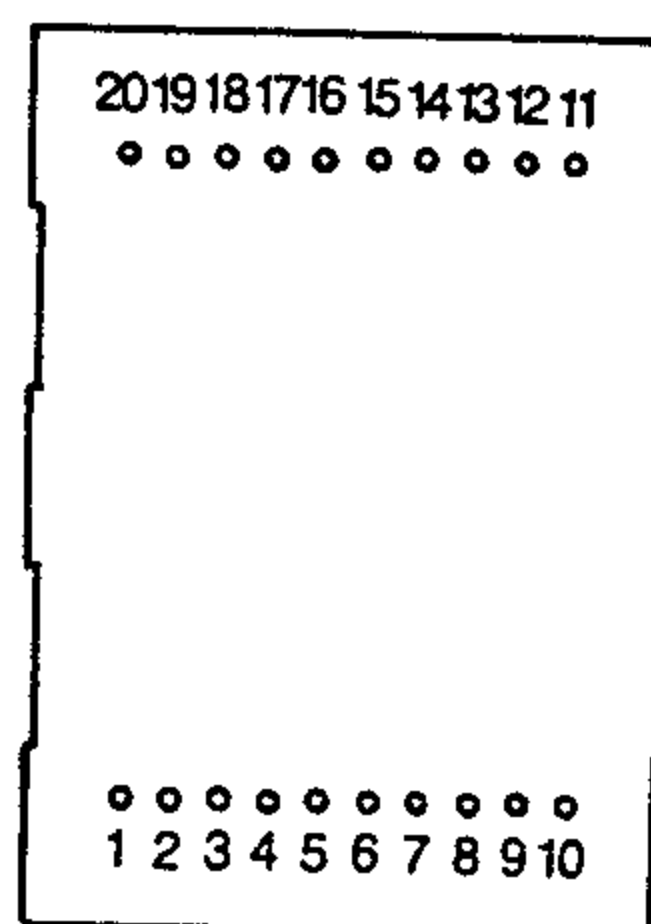
The SMD-5572 and the SMD-5579 series are an epoxy molded 2.0 inch (50.8mm) height, 5mm diameter and 5x7 dot matrix dual color LED displays. A red and green chips are contained in each dots and it could be displayed in red or green color separately and also appears in amber color when drive to red and green in the same time.

FEATURES

1. High brightness with high contrast
2. Wide angle viewing
3. Low power consumption;
Directly drive with I.C
4. Solid state reliability
Long operation life
5. Cathode- row (SDM5572) and cathode column (SDM5579) types available

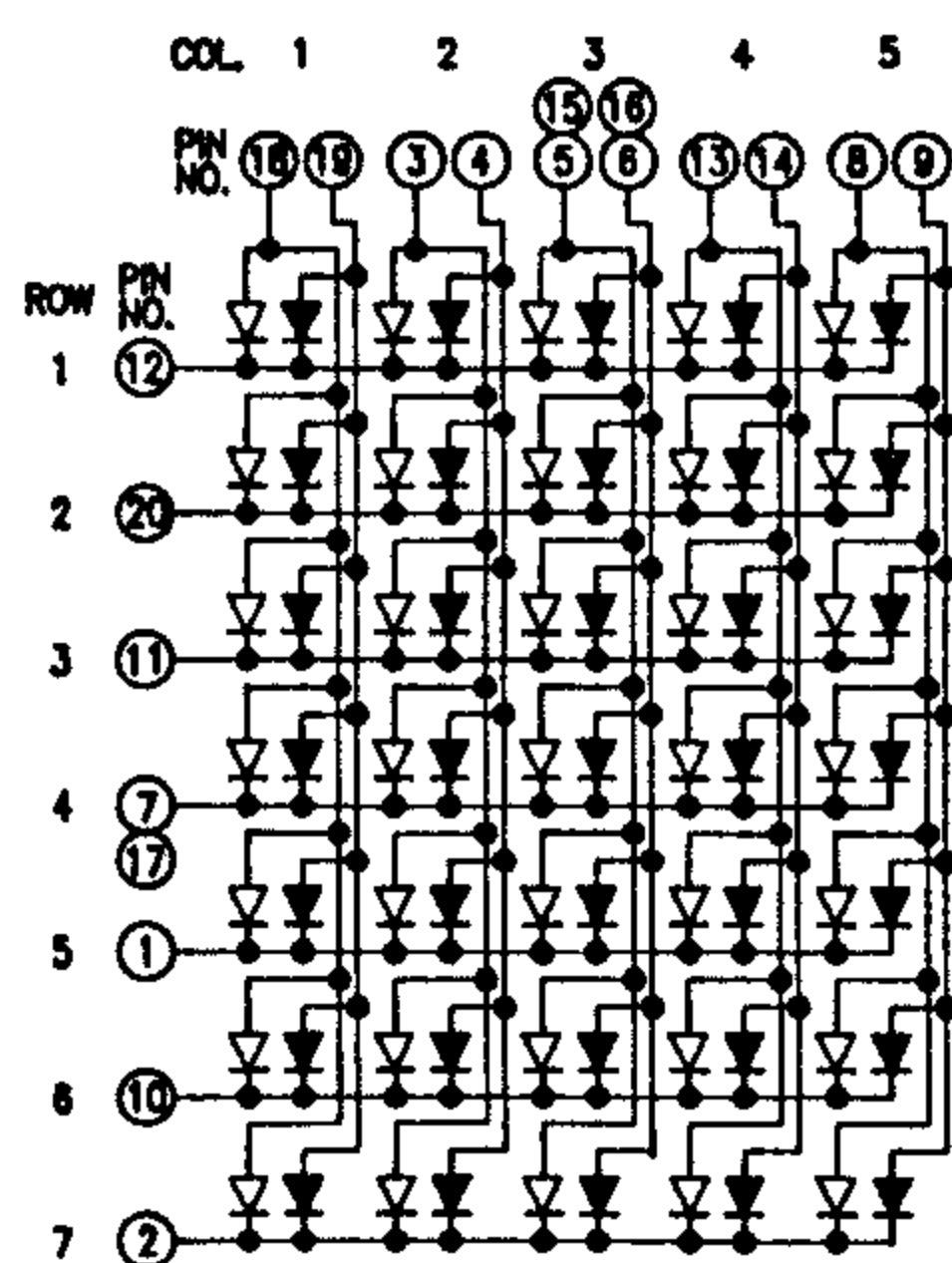
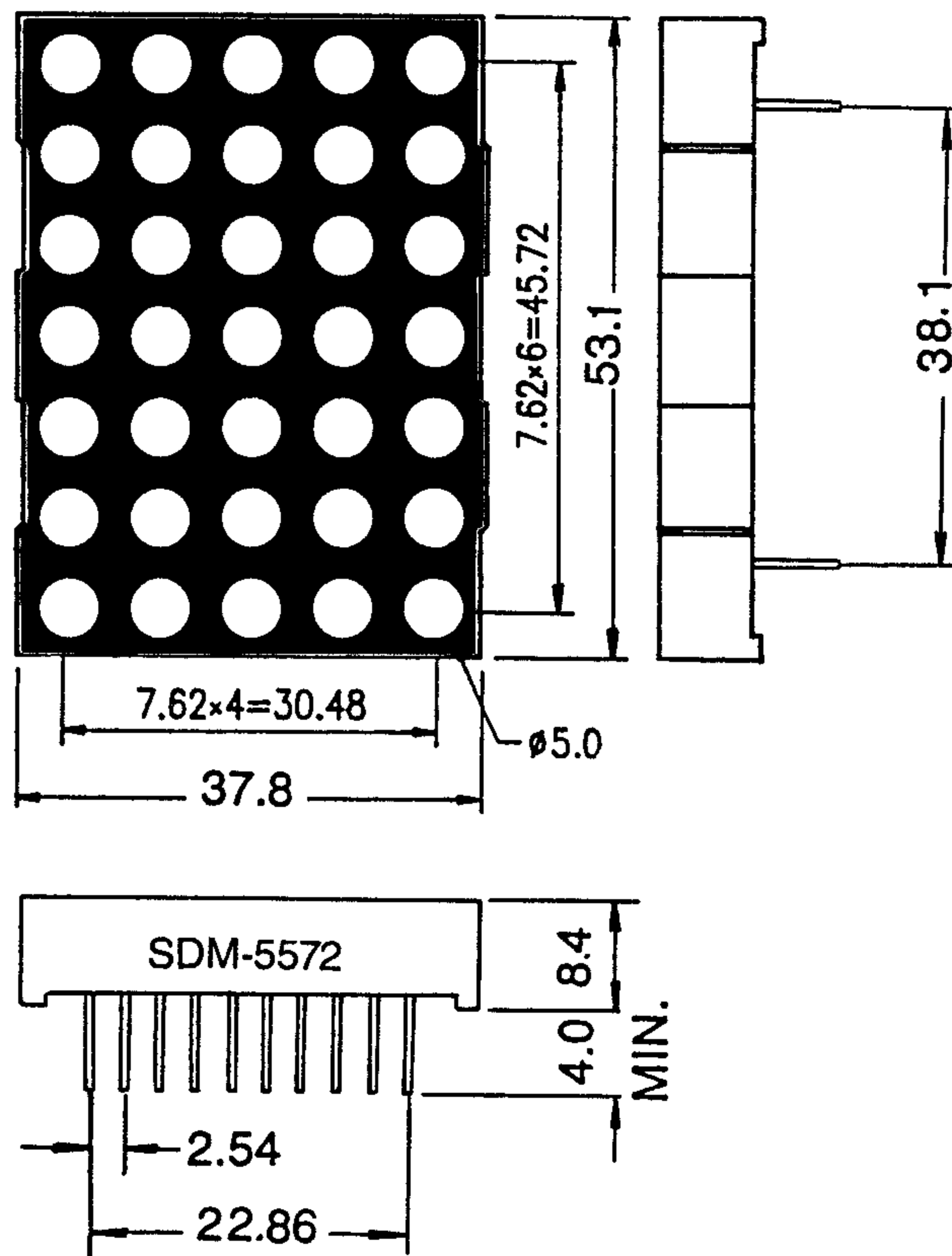
PIN ARRANGEMENTS


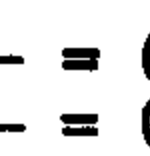
(Top View)

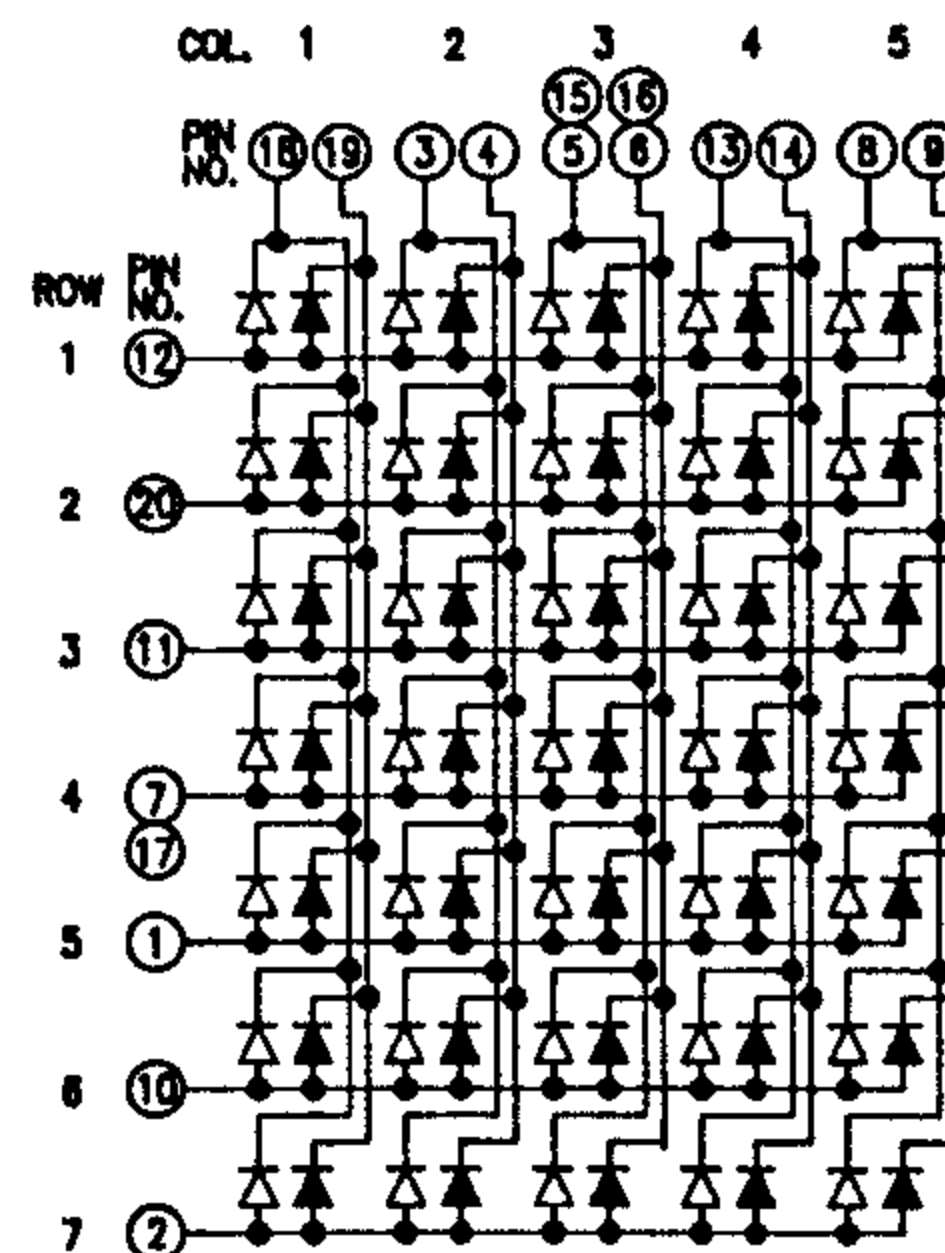


PACKAGE DIMENSIONS

SCALE 1:1 (mm)



 = GREEN
 = ORANGE



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SDM 5572/5579 SR-UG (GaAsP/GaP-GaP)

Orange SR SIDE (GaAsP/Gap)

Absolute Maximum Ratings (T_a = 25°C)

Power dissipation/Total	1000	mW
Power dissipation/Chip	30	mW
Forward current	15	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	°C
Storage temperature	-55 ~ +100	°C

Electrical/Optical Characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V _F	I _F = 10mA	—	2.0	2.2	V
Reverse current/Chip	I _R	V _R = 4V	—	—	10	μA
Luminous Intensity/Chip	I _v	I _F = 10mA	500	1000	—	μcd
Peak wavelength	λ _P	I _F = 10mA	—	635	—	nm
Spectral line halfwidth	Δλ	I _F = 10mA	—	35	—	nm

Yellow-green UG SIDE (GaP)

Absolute Maximum Ratings (T_a = 25°C)

Power dissipation/Total	1000	mW
Power dissipation/Chip	30	mW
Forward current	15	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	°C
Storage temperature	-55 ~ +100	°C

Electrical/Optical Characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V _F	I _F = 10mA	—	2.1	2.3	V
Reverse current/Chip	I _R	V _R = 4V	—	—	10	μA
Luminous intensity/Chip	I _v	I _F = 10mA	600	1200	—	μcd
Peak wavelength	λ _P	I _F = 10mA	—	565	—	nm
Spectral line halfwidth	Δλ	I _F = 10mA	—	30	—	nm

* Pulse Width 1 ms
 Duty Cycle 1/5